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## Correction: Physical probing of quantum energy levels in a single indium arsenide (InAs) quantum dot

Moh'd Rezeq,<sup>\*ab</sup> Yawar Abbas,<sup>ab</sup> Boyu Wen,<sup>c</sup> Zbig Wasilewski<sup>c</sup> and Dayan Ban<sup>\*c</sup>Correction for 'Physical probing of quantum energy levels in a single indium arsenide (InAs) quantum dot' by Moh'd Rezeq *et al.*, *Nanoscale Adv.*, 2023, 5, 5562–5569, <https://doi.org/10.1039/D3NA00638G>.

The authors regret that in the original publication, eqn 2(a)–(c) contained errors. The correct equations are given below:

$$\left[ -\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} + V_x(x) \right] \phi(x) = \varepsilon_x \phi(x), \quad (2a)$$

$$\left[ -\frac{\hbar^2}{2m} \frac{\partial^2}{\partial y^2} + V_y(y) \right] \phi(y) = \varepsilon_y \phi(y), \quad (2b)$$

$$\left[ -\frac{\hbar^2}{2m} \frac{\partial^2}{\partial z^2} + V_z(z) \right] \phi(z) = \varepsilon_z \phi(z), \quad (2c)$$

In addition, in the first line of the Abstract, the abbreviation for molecular beam epitaxy is incorrectly listed as EBM instead of the correct abbreviation MBE. Lastly, in the first line on page 5565 in the original publication, there is a typographical error in the word “indicate...”. The correct sentence is the following: “This indicates a completely discharged QD.”

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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